

**In The Claims:**

Claim 1. (original) A non-volatile read only memory device, comprising:  
a word line formed over a substrate, wherein the word line includes a metal layer and a polysilicon line;  
a trapping layer located between the word line and the substrate; and  
a polysilicon protection line formed over the substrate, the protection line electrically connects the word line and a grounded doped region in the substrate, wherein a resistance of the polysilicon protection line is higher than that of the word line.

Claim 2. (original) The device of claim 1, wherein the resistance of the polysilicon protection line is higher than that of the polysilicon line of the word line.

Claim 3. (original) The device of claim 1, wherein the polysilicon protection line is connected to the grounded doped region through a contact.

Claim 4. (original) The device of claim 1, wherein the trapping layer includes a silicon oxide/silicon nitride/silicon oxide composite layer.

Claim 5. (original) The device of claim 1, wherein the metal layer includes tungsten silicide.

Claim 6. (original) the device of claim 1, wherein the polysilicon protection line is located above an isolation region.

Claim 7. (original) the device of claim 6, wherein the isolation region include a field oxide layer.

Claim 8. (original) The device of claim 1, wherein at least portion of the polysilicon protection line is formed over the grounded doped region.

**Claims 9-19 (canceled)**